

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L2	15403	aluminum same ((AlN or AlON) or (aluminum adj nitride) or (aluminum adj oxynitride))	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/25 15:05
2	BRS	L3	1663	2 same dielectric	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/25 15:05
3	BRS	L4	270	3 and capacitor	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/25 15:13
4	IS&R	L6	3625	(438/396).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/25 15:59
5	BRS	L7	28	6 and 2	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/25 16:04

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	IS&R	L8	83	(438/768).CCLS.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/25 16:08
7	BRS	L16	4	2 and 8	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/25 16:09
8	BRS	L17	2095	(AlN or AlON or (aluminum adj3 nitride) or (aluminum adj3 oxynitride)) with (dielectric)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/25 16:10
9	BRS	L18	288	17 and capacitor	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/25 16:11
10	BRS	L19	108	18 not 4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2003/01/25 16:11

DERWENT-ACC-NO: 2000-249412
DERWENT-WEEK: 200104
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TITLE: DRAM capacitor manufacturing method involves forming compound dielectric film comprising alumina layer and aluminum nitride layer, between upper and lower electrodes

INVENTOR: CHOI, S J; KIM, Y G ; LEE, J H ; LEE, S M

PATENT-ASSIGNEE: SAMSUNG ELECTRONICS CO LTD[SMSU]

PRIORITY-DATA: 1998KR-0032638 (August 12, 1998)

PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE
PAGES	MAIN-IPC	
JP 2000058777	February 25, 2000	N/A
009	H01L 027/108	
A	March 6, 2000	N/A
000	H01L 027/108	
KR 2000013654		
A		

APPLICATION-DATA:

PUB-NO	APPL-DESCRIPTOR	APPL-NO
APPL-DATE		
JP2000058777A	N/A	1998JP-0363259
December 21, 1998		
KR2000013654A	N/A	1998KR-0032638
August 12, 1998		

INT-CL (IPC): H01L021/8242; H01L027/108

ABSTRACTED-PUB-NO: JP2000058777A

BASIC-ABSTRACT: NOVELTY - A compound dielectric film (115) comprising alumina layer and aluminum nitride layer, is formed between patterned polysilicon lower electrode (102) and upper electrode (105) by atomic layer deposition (ALD).

DETAILED DESCRIPTION - An INDEPENDENT CLAIM is also

included for DRAM
capacitor.

USE - For manufacture of DRAM capacitor.

ADVANTAGE - Since polysilicon electrodes are provided,
permutation caused by
electrodes does not generate chemical reaction. Since
dielectric film has high
dielectric constant, favorable oxidation property and
excellent insulating
property are obtained.

DESCRIPTION OF DRAWING(S) - The figure shows the sectional
view of DRAM
capacitor.

Polysilicon lower electrode 102

Polysilicon upper electrode 105

Compound dielectric film 115

CHOSEN-DRAWING: Dwg.3/13

TITLE-TERMS:

DRAM CAPACITOR MANUFACTURE METHOD FORMING COMPOUND
DIELECTRIC FILM COMPRISE
ALUMINA LAYER NITRIDE LAYER UPPER LOWER ELECTRODE

DERWENT-CLASS: L03 U11 U13 U14

CPI-CODES: L04-C14A;

EPI-CODES: U11-C18B5; U13-C04B1A; U14-A03B4;

SECONDARY-ACC-NO:

CPI Secondary Accession Numbers: C2000-075843

Non-CPI Secondary Accession Numbers: N2000-186971